

N-Channel Power MOSFET

700V, 6A, 0.75Ω

FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

KEY PERFORMANCE PARAMETERS				
PARAMETER	VALUE	UNIT		
V_{DS}	700	V		
R _{DS(on)} (max)	0.75	Ω		
Q_g	10.7	nC		

Pb





APPLICATION

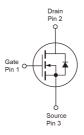
- Power Supply
- Lighting

TO-251 (IPAK)









Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _C = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$. I _D	6	
	$T_C = 100$ °C		3.6	A
Pulsed Drain Current (Note 2)		I _{DM}	18	А
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	62.5	W
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	81	mJ
Single Pulsed Avalanche Current (Note 3)		I _{AS}	1.8	А
Operating Junction and Storage Temperature	e Range	T_J,T_STG	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	2.0	°C/W	
Junction to Ambient Thermal Resistance	R _{OJA}	62	°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.





ELECTRICAL SPECIFICATIONS (T _C = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	700			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	2	3	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.8A$	R _{DS(on)}		0.62	0.75	Ω
Dynamic (Note 5)						
Total Gate Charge		Qg		10.7		
Gate-Source Charge	$V_{DS} = 380V, I_D = 6A,$ $V_{GS} = 10V$	Q_{gs}		2.8		nC
Gate-Drain Charge		Q_{gd}		3.5		
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C _{iss}		555		. –
Output Capacitance	f = 1.0MHz	C _{oss}		39		pF
Gate Resistance	f = 1MHz, open drain	R _g		2.7		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		15		
Turn-On Rise Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_D = 6A, V_{GS} = 10V,$	t _r		26		
Turn-Off Delay Time		t _{d(off)}		30		ns
Turn-Off Fall Time	$V_{GS} = V_{OV}$	t _f		18		
Source-Drain Diode (Note 4)						
Forward On Voltage	I _S = 6A, V _{GS} = 0V	V _{SD}			1.4	V
Reverse Recovery Time	$V_R = 200V, I_S = 3A$ $dI_F/dt = 100A/\mu s$	t _{rr}		182		ns
Reverse Recovery Charge		Q _{rr}		1.3		μC

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 50mH, $I_{AS} = 1.8A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.





ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM70N750CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM70N750CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

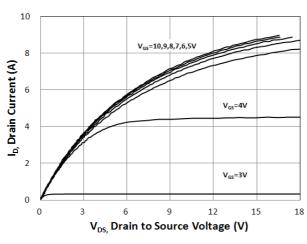
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



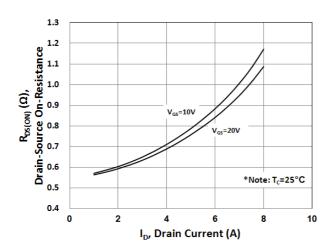
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

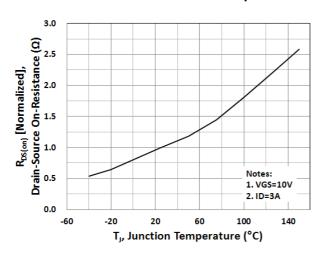
Output Characteristics



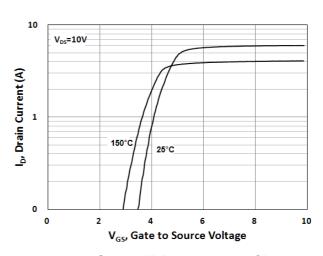
On-Resistance vs. Drain Current



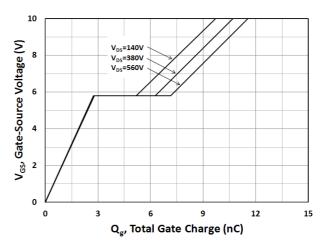
On-Resistance vs. Junction Temperature



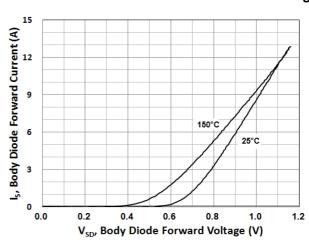
Transfer Characteristics



Gate-Source Voltage vs. Gate Charge



Source-Drain Diode Forward Current vs. Voltage

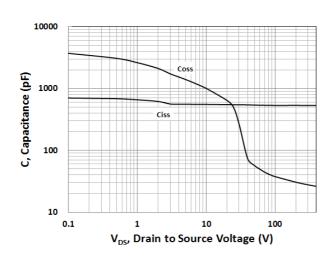




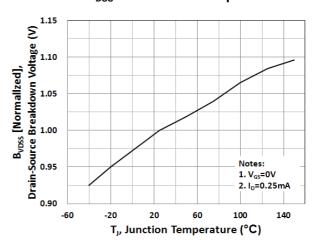
CHARACTERISTICS CURVES

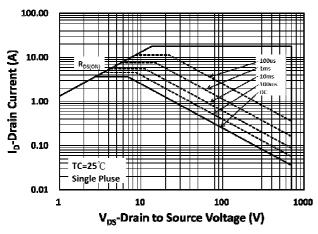
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

Capacitance vs. Drain-Source Voltage



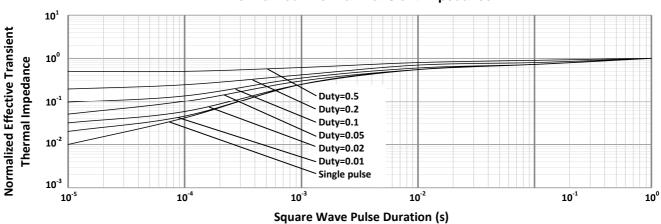
BV_{DSS} vs. Junction Temperature





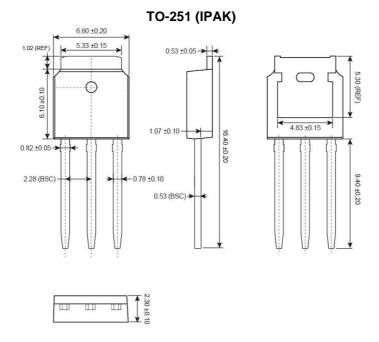
Maximum Safe Operating Area (DPAK/IPAK)

Normalized Thermal Transient Impedance

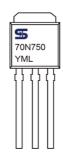




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

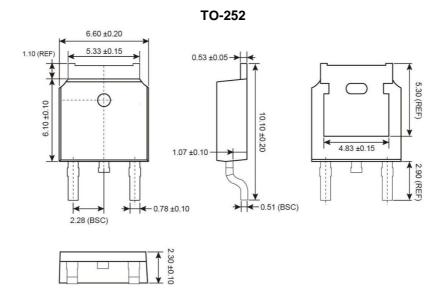
 $oldsymbol{O}$ =Jan $oldsymbol{P}$ =Feb $oldsymbol{Q}$ =Mar $oldsymbol{R}$ =Apr $oldsymbol{S}$ =May $oldsymbol{T}$ =Jun $oldsymbol{U}$ =Jul $oldsymbol{V}$ =Aug

W = Sep X = Oct Y = Nov Z = Dec

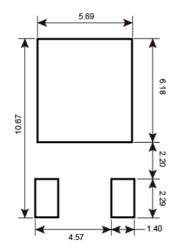
L = Lot Code (1~9, A~Z)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

 $L = \text{Lot Code } (1\sim 9, A\sim Z)$



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